



PATENT
Attorney Docket No. ASC-022CPC1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: Wu *et al.*

SERIAL NO.: 10/603,852 GROUP NO.: 3708

FILING DATE: June 25, 2003 EXAMINER: Owens

TITLE: ETCH STOP LAYER SYSTEM

Mail Stop: Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the patents and publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. Copies of the patents and publications are enclosed.

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

(1) within three (3) months of the **filings date** of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the **date of entry of the national stage** as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the **first Office action** on the merits, or before the mailing of a **first Office action** after the filing of a request for continued examination under 37 C.F.R. 1.114; or

(2) after the period defined in (1) but before the mailing date of a **final action** or a **notice of allowance** under 37 C.F.R. 1.311, and

the requisite Statement is below, **OR**

the requisite fee under 37 C.F.R. 1.17(p), namely **\$180.00**, is included herein, or

(3) after the mailing date of a **final action or notice of allowance** but before the payment of the **issue fee**, **AND**

the requisite Statement is below, **AND**

the requisite petition fee under 37 C.F.R. 1.17(p), namely **\$180.00** is included herein.

It is respectfully requested that each of the patents and publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application.

In addition, Applicants wish to inform the Examiner about the following co-pending patent applications and Office Actions cited therein:

- 1) U.S. Serial No. 09/611,024 (Docket No. ASC-023) filed on 06/07/2000, by Fitzgerald;
- 2) U.S. Serial No. 10/611,739 (Docket No. ASC-044C1) filed on 07/01/2003, by Fitzgerald *et al.*;
- 3) U.S. Serial No. 10/774,890 (Docket No. ASC-049C1) filed on 02/09/2004, by Fitzgerald;
- 4) U.S. Serial No. 10/802,185 (Docket No. ASC-025DVC1) filed on 03/17/2004, by Cheng *et al.*;
- 5) U.S. Serial No. 10/802,186 (Docket No. ASC-025DV2C1) filed on 03/17/2004, by Cheng *et al.*;
- 6) U.S. Serial No. 10/826,156 (Docket No. ASC-023C2) filed on 04/16/2004, by Fitzgerald; and
- 7) U.S. Serial No. 10/854,556 (Docket No. ASC-054C1) filed on 05/26/2004, by Fitzgerald.

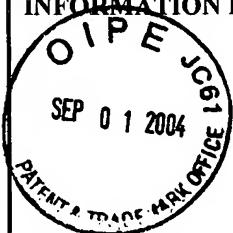
Respectfully submitted,

Date: August 30, 2004
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FORM PTO - 1449 INFORMATION DISCLOSURE STATEMENT 				ATTY DOCKET NO.: ASC-022CPC1 APPLICANT: Wu <i>et al.</i> SERIAL NO.: 10/603,852 FILING DATE: June 25, 2003 EXAMINER: Owens, Douglas W. GROUP: 2811			
U.S. PATENT DOCUMENTS							
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A70	2001/0003364	06/14/2001	Sugawara <i>et al.</i>			
	A71	2001/0007789	07/12/2001	Aspar <i>et al.</i>			
	A72	2002/0043660	04/18/2002	Yamazaki <i>et al.</i>			
	A73	2002/0084000	07/04/2002	Fitzgerald			
	A74	2002/0096717	07/25/2002	Chu <i>et al.</i>			
	A75	2002/0100942	08/01/2002	Fitzgerald <i>et al.</i>			
	A76	2002/0123167	09/05/2002	Fitzgerald			
	A77	2002/0123183	09/05/2002	Fitzgerald			
	A78	2002/0125471	09/12/2002	Fitzgerald <i>et al.</i>			
	A79	2002/0168864	11/14/2002	Cheng <i>et al.</i>			
	A80	2003/0003679	01/02/2003	Doyle <i>et al.</i>			
	A81	2003/0013305	01/16/2003	Sugii <i>et al.</i>			
	A82	2003/0034529	02/20/2003	Fitzgerald <i>et al.</i>			
	A83	2003/0057439	03/27/2003	Fitzgerald			
	A84	2003/0102498	06/05/2003	Braithwaite <i>et al.</i>			
	A85	2003/0119280	06/26/2003	Lee <i>et al.</i>			12/02/2002
	A86	2003/0127646	07/10/2003	Christiansen <i>et al.</i>			12/18/2002
	A87	2003/0139000	07/24/2003	Bedell <i>et al.</i>			01/23/2002
	A88	2003/0157787	08/21/2003	Murthy <i>et al.</i>			02/21/2002
	A89	2003/0160300	08/28/2003	Takenaka <i>et al.</i>			02/24/2003
	A90	2003/0178681	09/25/2003	Clark <i>et al.</i>			04/02/2003
	A91	2003/0189229	10/09/2003	Mouli			04/05/2002
	A92	2003/0199126	10/23/2003	Chu <i>et al.</i>			04/23/2002
EXAMINER				DATE CONSIDERED			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A93	2003/0201458	10/30/2003	Clark <i>et al.</i>			05/16/2003	
	A94	2003/0203600	10/30/2003	Chu <i>et al.</i>			06/15/2003	
	A95	2003/0207127	11/06/2003	Murthy <i>et al.</i>			05/30/2003	
	A96	2003/0215990	11/20/2003	Fitzgerald <i>et al.</i>			03/14/2003	
	A97	2003/0218189	11/27/2003	Christiansen			11/19/2002	
	A98	2003/0219957	11/27/2003	Kuwabara <i>et al.</i>			05/29/2003	
	A99	2003/0227036	12/11/2003	Sugiyama <i>et al.</i>			02/21/2003	
	A100	2003/0227057	12/01/2003	Lochtefeld <i>et al.</i>			10/04/2002	
	A101	2003/0230778	12/18/2003	Park <i>et al.</i>			01/30/2003	
	A102	2003/0232467	12/18/2003	Anderson <i>et al.</i>			05/29/2003	
	A103	2004/0005740	01/01/2004	Lochtefeld <i>et al.</i>			06/06/2003	
	A104	2004/0007724	01/15/2004	Murthy <i>et al.</i>			07/12/2002	
	A105	2004/0009649	01/15/2004	Kub <i>et al.</i>			05/20/2003	
	A106	2004/0012037	01/22/2004	Venkatesan <i>et al.</i>			07/18/2002	
	A107	2004/0012075	01/22/2004	Bedell <i>et al.</i>			07/16/2002	
	A108	2004/0014304	01/22/2004	Bhattacharyya			07/18/2002	
	A109	2004/0018699	01/29/2004	Boyd <i>et al.</i>			07/24/2002	
	A110	2004/0031979	02/19/2004	Lochtefeld			06/06/2003	
	A111	2004/0031990	02/19/2004	Jin <i>et al.</i>			08/16/2002	
	A112	2004/0041174	03/04/2004	Okihara			03/21/2003	
	A113	2004/0041210	03/04/2004	Mouli			09/02/2003	
	A114	2004/0048091	03/11/2004	Sato <i>et al.</i>			09/04/2003	
	A115	2004/0048454	03/11/2004	Sakaguchi			09/04/2003	
EXAMINER					DATE CONSIDERED			

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U.S. PATENT DOCUMENTS								
EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A116	2004/0051140	03/18/2004	Bhattacharyya			09/12/2002	
	A117	2004/0053477	03/18/2004	Ghyselen <i>et al.</i>			07/09/2003	
	A118	2004/0075149	04/22/2004	Fitzgerald <i>et al.</i>			07/23/2003	
	A119	4,704,302	11/03/1987	Bruel <i>et al.</i>				
	A120	4,710,788	12/01/1987	Dambkes <i>et al.</i>				
	A121	4,987,462	01/22/1991	Kim <i>et al.</i>				
	A122	4,990,979	02/05/1991	Otto				
	A123	4,997,776	03/05/1991	Harame <i>et al.</i>				
	A124	5,155,571	10/13/1992	Wang <i>et al.</i>				
	A125	5,177,583	01/05/1993	Endo <i>et al.</i>				
	A126	5,240,876	08/34/1993	Gaul <i>et al.</i>				
	A127	5,241,197	08/31/1993	Murakami <i>et al.</i>				
	A128	5,250,445	10/05/1993	Bean <i>et al.</i>				
	A129	5,291,439	03/01/1994	Kauffmann <i>et al.</i>				
	A130	5,298,452	03/29/1994	Meyerson				
	A131	5,316,958	05/31/1994	Meyerson				
	A132	5,399,522	03/21/1995	Ohori				
	A133	5,424,243	06/13/1995	Takasaki				
	A134	5,426,069	06/20/1995	Selvakumar <i>et al.</i>				
	A135	5,426,316	06/20/1995	Mohammad				
	A136	5,439,843	08/08/1995	Sakaguchi <i>et al.</i>				
	A137	5,461,250	10/24/1995	Burghartz <i>et al.</i>				
	A138	5,479,033	12/26/1995	Baca <i>et al.</i>				
EXAMINER					DATE CONSIDERED			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A139	5,523,243	06/04/1996	Mohammad			
	A140	5,572,043	11/05/1996	Shimizu <i>et al.</i>			
	A141	5,596,527	01/21/1997	Tomioka <i>et al.</i>			
	A142	5,617,351	04/01/1997	Bertin <i>et al.</i>			
	A143	5,630,905	05/20/1997	Lynch <i>et al.</i>			
	A144	5,659,187	08/19/1997	Legoues <i>et al.</i>			
	A145	5,698,869	12/16/1997	Yoshimi <i>et al.</i>			
	A146	5,714,777	02/03/1998	Ismail <i>et al.</i>			
	A147	5,739,567	04/14/1998	Wong			
	A148	5,777,347	07/07/1998	Bartelink			
	A149	5,786,612	07/28/1998	Otani <i>et al.</i>			
	A150	5,786,614	07/28/1998	Chuang <i>et al.</i>			
	A151	5,808,344	09/15/1998	Ismail <i>et al.</i>			
	A152	5,847,419	12/08/1998	Imai <i>et al.</i>			
	A153	5,863,830	01/26/1999	Bruel <i>et al.</i>			
	A154	5,882,987	03/16/1999	Srikrishnan			
	A155	5,912,479	06/15/1999	Mori <i>et al.</i>			
	A156	5,963,817	10/05/1999	Chu <i>et al.</i>			
	A157	5,993,677	11/30/1999	Biasse <i>et al.</i>			
	A158	6,013,134	01/11/2000	Chu <i>et al.</i>			
	A159	6,013,563	01/11/2000	Henley <i>et al.</i>			
	A160	6,020,252	02/01/2000	Aspar <i>et al.</i>			
	A161	6,058,044	05/02/2000	Sugiura <i>et al.</i>			
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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A162	6,103,597	08/15/2000	Aspar <i>et al.</i>			
	A163	6,103,599	08/15/2000	Henley <i>et al.</i>			
	A164	6,130,453	10/10/2000	Mei <i>et al.</i>			
	A165	6,133,799	10/17/2000	Favors <i>et al.</i>			
	A166	6,140,687	10/31/2000	Shimomura <i>et al.</i>			
	A167	6,143,636	11/07/2000	Forbes <i>et al.</i>			
	A168	6,160,303	12/12/2000	Fattaruso			
	A169	6,162,705	12/19/2000	Henley <i>et al.</i>			
	A170	6,190,998 B1	02/20/2001	Bruel <i>et al.</i>			
	A171	6,204,529	03/20/2001	Lung <i>et al.</i>			
	A172	6,225,192 B1	05/01/2001	Aspar <i>et al.</i>			
	A173	6,242,324	06/05/2001	Kub <i>et al.</i>			
	A174	6,249,022	06/19/2001	Lin <i>et al.</i>			
	A175	6,251,751 B1	06/26/2001	Chu <i>et al.</i>			
	A176	6,266,278	07/24/2001	Harari <i>et al.</i>			
	A177	6,271,551	08/07/2001	Schmitz <i>et al.</i>			
	A178	6,271,726	08/07/2001	Fransis <i>et al.</i>			
	A179	6,290,804 B1	09/18/2001	Henley <i>et al.</i>			
	A180	6,303,468 B1	10/16/2001	Aspar <i>et al.</i>			
	A181	6,316,301	11/13/2001	Kant			
	A182	6,326,667 B1	12/04/2001	Sugiyama <i>et al.</i>			
	A183	6,329,063	12/11/2001	Lo <i>et al.</i>			
	A184	6,339,232	01/15/2002	Takagi			
EXAMINER				DATE CONSIDERED			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A185	6,344,417 B1	02/05/2002	Usenko			
	A186	6,346,459 B1	02/12/2002	Usenko <i>et al.</i>			
	A187	6,352,909	03/05/2002	Usenko			
	A188	6,355,493 B1	03/12/2002	Usenko			
	A189	6,368,938 B1	04/09/2002	Usenko			
	A190	6,369,438 B1	04/09/2002	Sugiyama <i>et al.</i>			
	A191	6,372,593	04/16/2002	Hattori <i>et al.</i>			
	A192	6,372,609 B1	04/16/2002	Aga <i>et al.</i>			
	A193	6,387,829 B1	05/14/2002	Usenko <i>et al.</i>			
	A194	6,391,740 B1	05/21/2002	Cheung <i>et al.</i>			
	A195	6,399,970	06/04/2002	Kubo <i>et al.</i>			
	A196	6,403,975	06/11/2002	Brunner <i>et al.</i>			
	A197	6,407,406	06/18/2002	Tezuka			
	A198	6,410,371 B1	06/25/2002	Yu <i>et al.</i>			
	A199	6,420,937	07/16/2002	Akatsuka <i>et al.</i>			
	A200	6,425,951	07/30/2002	Chu <i>et al.</i>			
	A201	6,429,061	08/06/2002	Rim			
	A202	6,445,016 B1	09/03/2002	An <i>et al.</i>			
	A203	6,448,152 B1	09/10/2002	Henley <i>et al.</i>			
	A204	6,455,397 B1	09/24/2002	Belford			
	A205	6,458,672 B1	10/01/2002	Henley <i>et al.</i>			
	A206	6,475,072 B1	11/05/2002	Canaperi <i>et al.</i>			
	A207	6,514,836 B2	02/04/2003	Belford			
EXAMINER				DATE CONSIDERED			

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EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE	
	A208	6,515,335 B1	02/04/2003	Christiansen <i>et al.</i>				
	A209	6,524,935	02/25/2003	Canaperi <i>et al.</i>				
	A210	6,534,381 B2	03/18/2003	Cheung <i>et al.</i>				
	A211	6,555,839	04/29/2003	Fitzgerald				
	A212	6,583,437 B2	06/24/2003	Mizuno <i>et al.</i>				
	A213	6,593,191	07/15/2003	Fitzgerald			01/17/2001	
	A214	6,593,625 B2	07/15/2003	Christiansen <i>et al.</i>			04/03/2002	
	A215	6,596,610 B1	07/22/2003	Kuwabara <i>et al.</i>			11/27/2000	
	A216	6,602,613	08/05/2003	Fitzgerald			05/16/2000	
	A217	6,603,156	08/05/2003	Rim			03/31/2001	
	A218	6,607,948 B1	08/19/2003	Sugiyama <i>et al.</i>			08/24/2001	
	A219	6,624,047 B1	09/23/2003	Sakaguchi <i>et al.</i>			02/01/2000	
	A220	6,624,478 B2	09/23/2003	Anderson <i>et al.</i>			01/30/2002	
	A221	6,632,724 B2	10/14/2003	Henley <i>et al.</i>			01/13/2000	
	A222	6,635,909 B2	10/21/2003	Clark <i>et al.</i>			03/19/2002	
	A223	6,645,831 B1	11/11/2003	Shaheen <i>et al.</i>			05/07/2002	
	A224	6,646,322	11/11/2003	Fitzgerald			07/16/2001	
	A225	6,649,480	11/18/2003	Fitzgerald <i>et al.</i>			06/19/2001	
	A226	6,649,492 B2	11/18/2003	Chu <i>et al.</i>			02/11/2002	
	A227	6,656,271 B2	12/02/2003	Yonchara <i>et al.</i>			12/03/1999	
	A228	6,664,169 B1	12/16/2003	Iwasaki <i>et al.</i>			06/05/2000	
	A229	6,677,183 B2	01/13/2004	Sakaguchi <i>et al.</i>			01/31/2002	
	A230	6,677,192	01/13/2004	Fitzgerald			07/16/2001	
EXAMINER					DATE CONSIDERED			

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INFORMATION DISCLOSURE STATEMENT		APPLICANT: Wu <i>et al.</i>	
		SERIAL NO.: 10/603,852	
		FILING DATE: June 25, 2003	
		EXAMINER: Owens, Douglas W.	
		GROUP: 2811	

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	A231	6,680,240 B1	01/20/2004	Maszara			06/25/2002
	A232	6,680,260 B2	01/20/2004	Akiyama <i>et al.</i>			09/17/2002
	A233	6,690,043 B1	02/10/2004	Usuda <i>et al.</i>			11/22/2000
	A234	6,703,144	03/09/2004	Fitzgerald			03/18/2003
	A235	6,703,688	03/09/2004	Fitzgerald			07/16/2001
	A236	6,706,614 B1	03/16/2004	An <i>et al.</i>			05/15/2002
	A237	6,706,618 B2	03/16/2004	Takisawa <i>et al.</i>			07/29/2002
	A238	6,707,106 B1	03/16/2004	Wristers <i>et al.</i>			10/18/2002
	A239	6,709,903	03/23/2004	Christiansen			04/30/2003
	A240	6,709,909 B2	03/23/2004	Mizuno <i>et al.</i>			05/19/2003
	A241	6,713,326	03/30/2004	Cheng <i>et al.</i>			03/04/2003
	A242	6,723,661	04/20/2004	Fitzgerald			07/16/2001
	A243	6,730,551	05/04/2004	Lee <i>et al.</i>			08/02/2002
	A244	6,737,670	05/18/2004	Cheng <i>et al.</i>			03/07/2003
	A245	6,750,130	06/15/2004	Fitzgerald			01/07/2001

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B9	41 01 167	07/23/1992	DE				N	Y (Abstract only)
	B10	0 514 018	11/19/1992	EP				N	Y
	B11	0 829 908	03/18/1998	EP				N	Y
	B12	0 838 858	04/29/1998	EP				N	N
	B13	1 020 900	07/19/2000	EP				N	Y

EXAMINER**DATE CONSIDERED**

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FOREIGN PATENT DOCUMENTS									
EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
	B14	1 174 928	01/23/2002	EP				N	Y
	B15	2 701 599	09/01/1993	FR				Y	Y
	B16	2 342 777	04/19/2000	GB				Y	Y
	B17	61/141116	06/28/1986	JP				N	Y (Abstract only)
	B18	2/210816	08/22/1990	JP				N	Y (Abstract only)
	B19	3/036717	02/18/1991	JP				N	Y
	B20	4-307974	10/30/1992	JP				N	N
	B21	5-166724	07/23/1993	JP				N	Y (Abstract only)
	B22	6-177046	06/24/1994	JP				N	Y (Abstract only)
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	B26	7-106446	04/21/1995	JP				N	N
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	B38	01/93338	12/06/2001	WO				N	Y
	B39	02/13262	02/14/2002	WO				N	Y
	B40	02/15244	02/21/2002	WO				N	Y
	B41	02/27783	04/04/2002	WO				N	Y
	B42	02/47168	06/13/2002	WO				N	Y
	B43	02/071488	09/12/2002	WO				N	Y
	B44	02/071491	09/12/2002	WO				N	Y
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	B47	04/006311	01/15/2004	WO				N	Y
	B48	04/006326	01/15/2004	WO				N	Y
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